

Attorney's Docket No.: 10559-879001/P17481 Intel Corporation

Examiner:

2851

R. Fuller

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Yan Borodovsky Art Unit:

Serial No.: 10/688,306

: October 17, 2003 Assignee : Intel Corporation

Title

Filed

: COMPOSITE PRINTING

Mail Stop Amendment

Commissioner for Patents

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INFORMATION DISCLOSURE STATEMENT

Dear Sir:

Applicants call attention to the attached Information Disclosure Statement and documents listed on form PTO-1449.

Kindly accept this Information Disclosure Statement under Rule 97(c)(2). The rule 17(p) certification fee of \$180 is enclosed.

The documents are in the English language; hence no concise explanation is necessary per Rule 98(a)(3).

Consideration of the foregoing and enclosures plus the return of a copy of the enclosed form PTO-1449 with the

CERTIFICATE OF MAILING BY FIRST CLASS MAIL

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Applicant : Yan Borodovsky

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Examiner's initials in the left column per MPEP 609 are earnestly solicited along with an early action on the merits.

Please apply any additional charges or credits to Deposit Account No. 06-1050.

Respectfully submitted,

Scott C. Harris Req. No. 32,030

Attorney for Intel Corporation

Attorney's Docket No.:10559-879001

Date: March 29, 2005

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Substitute Form PTO-1449 (Modified)	U.S. Department of Commerce Patent and Trademark Office	Attorney's Docket No. 10559-879001	Application No. 10/688,306	010
Information Disclosure Statement by Applicant (Use several sheets if necessary) (37 CFR §1.98(b))		Applicant Yan Borodovsky	MAP 3 1 2005 6	
		Filing Date October 17, 2003	Group Art Unit 2851	PAOEMARK (R. C.

U.S. Patent Documents							
Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
	AA						
	AB						
	AC						
	ΑĎ						

Foreign Patent Documents or Published Foreign Patent Applications								
Examiner	Desig.	Document	Publication	Country or			Trans	slation
Initial	ID	Number	Date	Patent Office	Class	Subclass	Yes	No
	AE							
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	AG	,						

	Other D	ocuments (include Author, Title, Date, and Place of Publication)
Examiner Initial	Desig. ID	Document
	АН	M. Fritze, et al., "Gratings of regular arrays and trim exposures for ultralarge scale integrated circuit phase-shift lithography", J. of Vacuum Science & Technology B, 19(6):2366-2370, Nov/Dec 2001.
	AI	J.A. Hoffnagle, et al., "Liquid immersion deep-ultraviolet interferometric lithography", J. of Vacuum Science & Technology B, 17(6):3306-3309, Nov/Dec 1999.
	AJ	Marc D. Levenson, et al., "Exposing the DUV SCAAM – 75 nm Imaging on the Cheap!", Proc. of SPIE: Design, Process Integration, and Characterization for Microelectronics, 4692:288-297, March 2002.
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	AL	Bruce W. Smith, et al., "Water immersion optical lithography at 193 nm", J. Microlith., Microfab., Microsyst., 3(1):44-51, Jan. 2004.
	AM	Akiyoshi Susuki, et al., "Multilevel imaging system realizing k ₁ +=0.3 lithography", <i>Proc. of SPIE:</i> Optical Microlithography XII, 3679:396-407, Mar. 1999.
	AN	M. Switkes, et al., "Extending optics to 50 nm and beyond with immersion lithography", J. of Vacuum Science & Technology B, 21(6):2794-2799, Nov/Dec 2003.
	AQ	Brian Tyrrell, et al., "Investigation of the physical and practical limits of dense-only phase shift lithography for circuit feature definition", <i>J. Microlith., Microfab., Microsyst.</i> , 1(3):244-252, Oct. 2002.
	AP	Saleem H. Zaidi, et al., "Multiple exposure interferometric lithography", Proc. of SPIE: Optical Microlithography VII, 2197:869-875, Mar. 1994.
,	AQ	M. Fritze, et al., "Preprint of poster presentation entitled "High-Throughput Hybrid Optical Maskless Lithography: All-Optical 32-nm Node Imaging,", Presented at SPIE Microlithography 2005, San Jose, California, USA, March 3, 2005.

Examiner Signature	Date Considered
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EXAMINER: Initials citation considered. Draw line through citation if no	of in conformance and not considered. Include copy of this form with
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